Application No.: Atty Docket No. Form 1449 (Modified) 09/648,095 KLA1P016F JAN 2 9 2001 Applicant: Information Disclosure Statement By Applicant Satya, et al Group Filing Date 2858 August 25, 2000 (Use Several Sheets if Necessary)

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Initial	No.	Patent No.	Date	Patentee	Class	class	Date
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	C3				
Examiner		Date Considered 10/31/02			

Examiner: Initial citation considered. Draw line through citation if not in conformance and Examiner: Initial citation considered. Draw line through citation in not in considered. Include copy of this form with next communication to applicant.